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Amendments to the Specification:

Please replace the paragraph beginning at page 5, line 7 with the following amended paragraph:

As shown in FIG. 7, the dielectric layer 111 is patterned with photoresist 115, then anisotropically reactive ion etching (RIE) is employed to etch the dielectric layer 111 to form a opening an opening 116, then a P+ doping with boron is performed in the predetermined P+ doping region 109 (as shown in FIG. 5) such that a P+ doped region 117 is formed. Dosage of the doping is between 10^{15} and 1×10^{16} atoms/cm². Energy of the doping is between 1 and 3 keV.